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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

Sheet 1 of 4

Application Number.: Unassigned
 Filing Date: Herewith
 First Named Inventor: Toshiharu Furukawa
 Art Unit: Unassigned
 Examiner Name: Unassigned
 Attorney Docket Number.: ROC920030271US1

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns or Lines Where Relevant Passages or Figs. Appear
		Number - Kind Code ² (if known)			
DN		US - 6.423.583 B1	07-23-2002	Avouris et al.	
		US - 6.515.325 B1	02-04-2003	Farnworth et al.	
		US - 2003/0168683 A1	09-11-2003	Farnworth et al.	
		US - 2003/0170930 A1	09-11-2003	Choi et al.	
		US - 2003/0178617 A1	09-25-2003	Appenzeller et al.	
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First Named Inventor:

Toshiharu Furukawa

Art Unit:

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Examiner Name:

Unassigned

Sheet 2 of 4

Attorney Docket Number.:

ROC920030271US1**OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS**

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ON		P. HARRIS, "Carbon Nanotubes and Related Structures," Cambridge University Press, 1999.	
		K. TEO et al., "Catalytic Synthesis of Carbon Nanotubes and Nanofibers," Encyclopedia of Nanoscience and Nanotechnology, Volume X, pp. 1-22, 2003.	
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		H. CUI et al., "Growth Behavior of Carbon Nanotubes on Multilayered Metal Catalyst Film in Chemical Vapor Deposition," Chemical Physics Letters 374 (2003), pp. 222-228.	
		J. LI et al., "Highly-Ordered Carbon Nanotube Arrays for Electronics Applications," Applied Physics Letters, Volume 75, Number 3, July 19, 1999, pp. 367-369.	
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 Art Unit: Unassigned
 Examiner Name: Unassigned
 Attorney Docket Number.: ROC920030271US1

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

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ON		V. DERYCKE et al., "Carbon Nanotube Inter- and Intramolecular Logic Gates," Nano Letters, xxx, Vol. 0, No. 0, A-D, received August 16, 2001.	
		P. COLLINS et al., "Nanotubes for Electronics," Scientific American, December 2000, pp. 62-69.	
		S. J. WIND et al., "Vertical Scaling of Carbon Nanotube Field-Effect Transistors Using Top Gate Electrodes," Applied Physics Letters, Volume 80, Number 20, May 20, 2002, pp. 3817-3819.	
		Z. F. REN et al., "Growth, Characterization, and Potential Applications of Periodic Carbon Nanotube Arrays," Department of Physics, Boston College, updated 2001.	
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		"Carbon Nanotube Arrays: Synthesis of Dense Arrays of Well-Aligned Carbon Nanotubes Completely Filled with Titanium Carbide on Titanium Substrates," Battelle No. 12132.	
		A. CHANG, "Integration of Nanotubes into Devices," National Nanofabrication Users Network, Stanford Nanofabrication Facility, p. 58.	
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		Z. REN et al., "Synthesis of Large Arrays of Well-Aligned Carbon Nanotubes on Glass," Science, Vol. 282, November 6, 1998, pp. 1105-1107.	
		Z. REN et al., "Large Arrays of Well-Aligned Carbon Nanotubes," Proceedings of 13th International Winter School on Electronic Properties of Novel Materials, pp. 263-267, February 27-March 6, 1999, Kirchberg / Tirol, Austria.	
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Application Number	10777576
Filing Date	2004-02-12
First Named Inventor	Toshiharu Furukawa
Art Unit	2811
Examiner Name	Ori Nadav
Attorney Docket Number	ROC920030271US

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)	Application Number		10777576
	Filing Date		2004-02-12
	First Named Inventor	Toshiharu Furukawa	
	Art Unit	2811	
	Examiner Name	Ori Nadav	
	Attorney Docket Number	ROC920030271US	

ON	1	THOMAS RUECKES, ET AL., Carbon Nanotube-Based Nonvolatile Random Access Memory for Molecular Computing, Science magazine, July 7, 2000, Pages 94-97, Vol. 289.	<input type="checkbox"/>
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